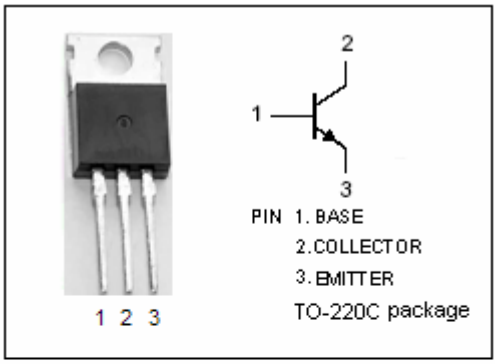
isc Silicon NPN Power Transistor KSD401

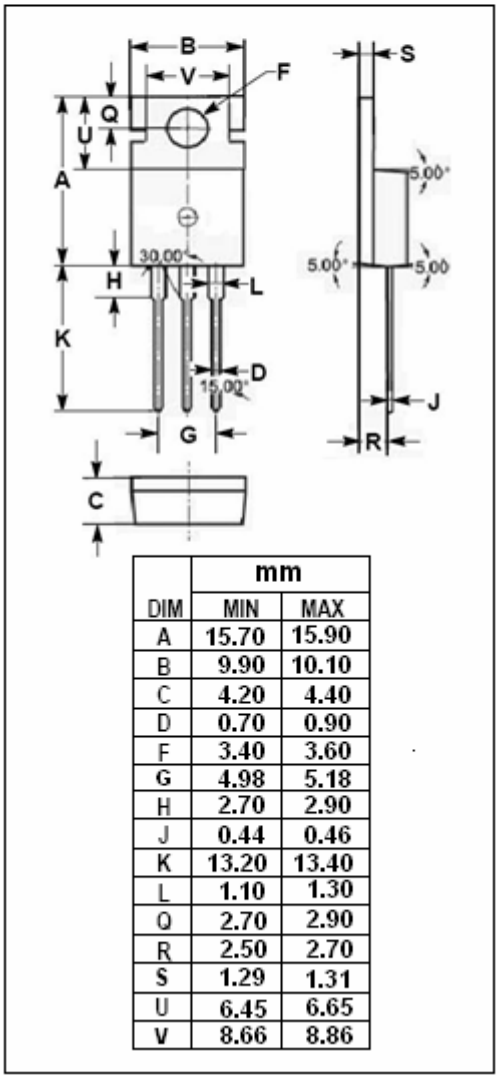


DESCRIPTION

- Collector-Base Breakdown Voltage-
  : $V_{(BR)CBO}$= 200V(Min)
- Collector Current- I_C= 2A
- Collector Power Dissipation-
  : P_C= 25W@ T_C= 25℃
- Complement to Type KSB546

APPLICATIONS

- Designed for TV Vertical deflection output applications.



DIM	mm MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	2	A
P_C	Collector Power Dissipation @ T_C=25℃	25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

isc Silicon NPN Power Transistor KSD401

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA ; I_B= 0	150			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 0.5mA ; I_E= 0	200			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 0.5mA; I_C= 0	5			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 0.5A; I_B= 50mA			1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 150V; I_E= 0			50	μA
h_{FE}	DC Current Gain	I_C= 0.4A; V_{CE}= 10V	40		400	
f_T	Current-Gain—Bandwidth Product	I_C= 0.4A; V_{CE}= 10V		5		MHz

◆ **h_{FE} Classifications**

R	O	Y	G
40-80	70-140	120-240	200-400